



EasyPIM™2B Modul PressFIT mit Trench/Feldstopp IGBT3 und Emitter Controlled3 Diode  
EasyPIM™2B module PressFIT with trench/fieldstop IGBT3 and Emitter Controlled3 Diode

初步数据  
Preliminary Data

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	600	V
连续集电极直流电流 Continuous DC collector current	$T_C = 75^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ $I_C$	50 65	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	$I_{CRM}$	100	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$P_{\text{tot}}$	175	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		$V_{GES}$	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.		
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 50\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 50\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 50\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,45 1,60 1,70	1,90	V V V	
栅极阈值电压 Gate threshold voltage	$I_C = 0,80\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{GE\text{th}}$	4,9	5,8	6,5	V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		$Q_G$	0,50			$\mu\text{C}$
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	0,0			$\Omega$
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{\text{ies}}$	3,10			nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{\text{res}}$	0,095			nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$			1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{on}}$	0,025 0,025 0,025			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
上升时间(电感负载) Rise time, inductive load	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_r$	0,015 0,018 0,02			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{off}}$	0,19 0,21 0,215			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
下降时间(电感负载) Fall time, inductive load	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_f$	0,10 0,135 0,14			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 2800\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{G\text{on}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{\text{on}}$	0,55 0,75 0,85			mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 4300\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{G\text{off}} = 8,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{\text{off}}$	1,20 1,50 1,60			mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 360\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{S\text{CE}} \cdot di/dt$	$t_P \leq 8\ \mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 6\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	$I_{SC}$	350 250			A A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		$R_{th\text{JC}}$	0,75	0,85		K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{th\text{CH}}$	0,70			K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

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初步数据  
Preliminary Data

二极管, 逆变器 / Diode, Inverter  
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	600	V
连续正向直流电流 Continuous DC forward current		$I_F$	50	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	$I_{FRM}$	100	A
$I^2t$ -值 $I^2t$ - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I^2t$	370 330	$\text{A}^2\text{s}$ $\text{A}^2\text{s}$

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 50\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 50\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_F$	1,55 1,50 1,45	1,95	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 50\text{ A}, -di_F/dt = 2800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$I_{RM}$	78,0 82,0 84,0		A A A
恢复电荷 Recovered charge	$I_F = 50\text{ A}, -di_F/dt = 2800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$Q_r$	2,25 4,00 4,40		$\mu\text{C}$ $\mu\text{C}$ $\mu\text{C}$
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 50\text{ A}, -di_F/dt = 2800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{rec}$	0,58 1,00 1,10		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		$R_{thJC}$	1,10	1,20	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	0,90		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

二极管, 整流器 / Diode, Rectifier  
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1600	V
最大正向均方根电流(每芯片) Maximum RMS forward current per chip	$T_C = 100^{\circ}\text{C}$	$I_{FRMSM}$	60	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	$T_C = 100^{\circ}\text{C}$	$I_{RMSM}$	60	A
正向浪涌电流 Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I_{FSM}$	450 370	A A
$I^2t$ -值 $I^2t$ - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I^2t$	1000 685	$\text{A}^2\text{s}$ $\text{A}^2\text{s}$

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 50\text{ A}$	$V_F$		1,05		V
反向电流 Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1600\text{ V}$	$I_R$		1,00		mA
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	$R_{thJC}$		1,05	1,15	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$	$R_{thCH}$		0,95		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$			$^{\circ}\text{C}$

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初步数据  
Preliminary Data

IGBT, 制动-斩波器 / IGBT, Brake-Chopper  
最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	600	V
连续集电极直流电流 Continuous DC collector current	$T_C = 75^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ $I_C$	50 65	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	$I_{CRM}$	100	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$P_{\text{tot}}$	175	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		$V_{GES}$	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.		
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 50\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 50\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 50\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,45 1,60 1,70	1,90	V V V	
栅极阈值电压 Gate threshold voltage	$I_C = 0,80\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{GEth}$	4,9	5,8	6,5	V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		$Q_G$	0,50			$\mu\text{C}$
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{Gint}$	0,0			$\Omega$
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{ies}$	3,10			nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{res}$	0,095			nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$			1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 18\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{don}$	0,045 0,045 0,045			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
上升时间(电感负载) Rise time, inductive load	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 18\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_r$	0,03 0,035 0,04			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 18\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{doff}$	0,31 0,32 0,33			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
下降时间(电感负载) Fall time, inductive load	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 18\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_f$	0,13 0,135 0,14			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 18\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{on}$	1,50 2,00 2,10			mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 50\text{ A}, V_{CE} = 300\text{ V}, L_S = 35\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 18\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{off}$	1,20 1,50 1,60			mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 360\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 8\ \mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 6\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	$I_{SC}$	350 250			A A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		$R_{thJC}$	0,75	0,85		K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1\text{ W/(m}\cdot\text{K)}$		$R_{thCH}$	0,70			K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	150		$^{\circ}\text{C}$

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初步数据  
Preliminary Data

二极管，制动-斩波器 / Diode, Brake-Chopper  
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	600	V
连续正向直流电流 Continuous DC forward current		$I_F$	15	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	$I_{FRM}$	30	A
$I_{2t}$ -值 $I_{2t}$ - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I_{2t}$	22,5 20,5	$\text{A}^2\text{s}$ $\text{A}^2\text{s}$

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 15\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 15\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 15\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_F$	1,60 1,55 1,50	2,00	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 15\text{ A}, -di_F/dt = 1600\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$I_{RM}$	23,0 25,0 26,0		A A A
恢复电荷 Recovered charge	$I_F = 15\text{ A}, -di_F/dt = 1600\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$Q_r$	0,80 1,40 1,70		$\mu\text{C}$ $\mu\text{C}$ $\mu\text{C}$
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 15\text{ A}, -di_F/dt = 1600\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{rec}$	0,16 0,28 0,37		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		$R_{thJC}$	2,25	2,50	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	1,40		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	$T_C = 25^{\circ}\text{C}$	$R_{25}$		5,00		$\text{k}\Omega$
R100 偏差 Deviation of R100	$T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5	%
耗散功率 Power dissipation	$T_C = 25^{\circ}\text{C}$	$P_{25}$			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

根据应用手册标定

Specification according to the valid application note.

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初步数据  
Preliminary Data

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V <sub>ISOL</sub>	2,5		kV
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al <sub>2</sub> O <sub>3</sub>		
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		11,5 6,3		mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		10,0 5,0		mm
相对电痕指数 Comperative tracking index		CTI	> 200		
			min.	typ.	max.
杂散电感,模块 Stray inductance module		L <sub>sCE</sub>		30	nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	T <sub>c</sub> = 25°C, 每个开关 / per switch	R <sub>CC'+EE'</sub> R <sub>AA'+CC'</sub>		5,00 6,00	mΩ
储存温度 Storage temperature		T <sub>stg</sub>	-40		125 °C
Anpresskraft für mech. Bef. pro Feder mounting force per clamp		F	40	-	80 N
重量 Weight		G		39	g

Der Strom im Dauerbetrieb ist auf 25 A effektiv pro Anschlusspin begrenzt.  
The current under continuous operation is limited to 25 A rms per connector pin.

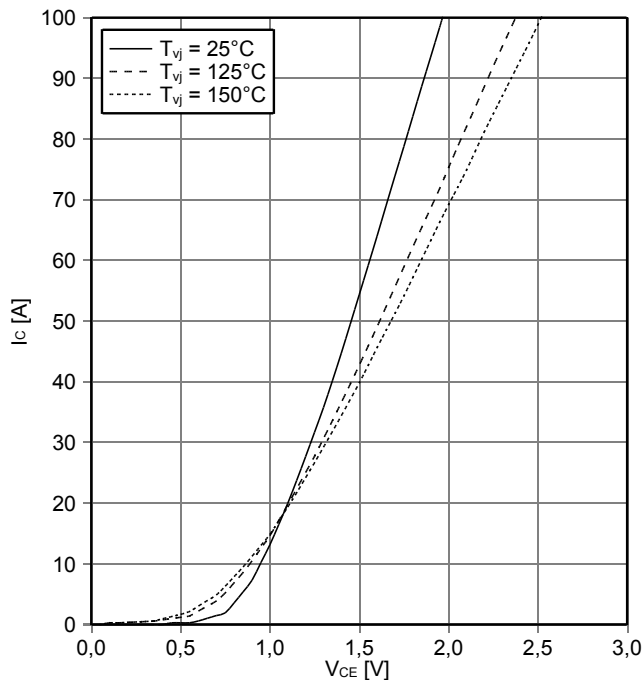
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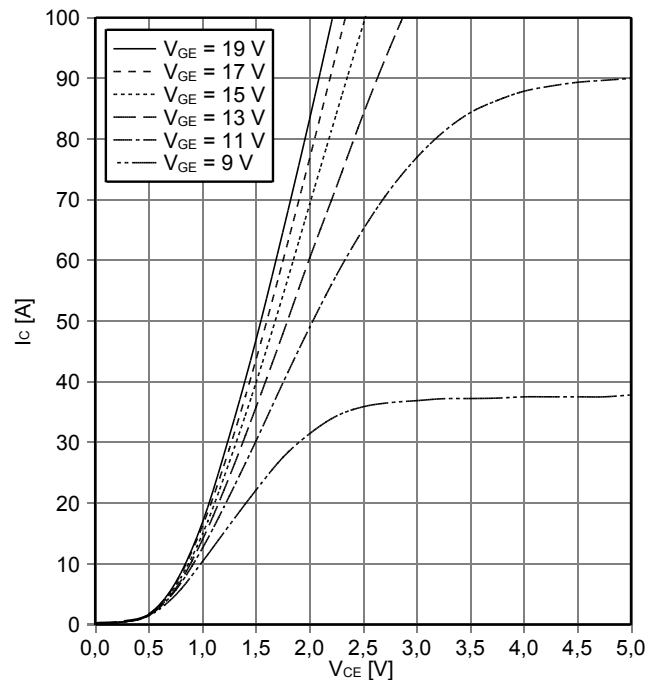
输出特性 IGBT, 逆变器 (典型)  
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



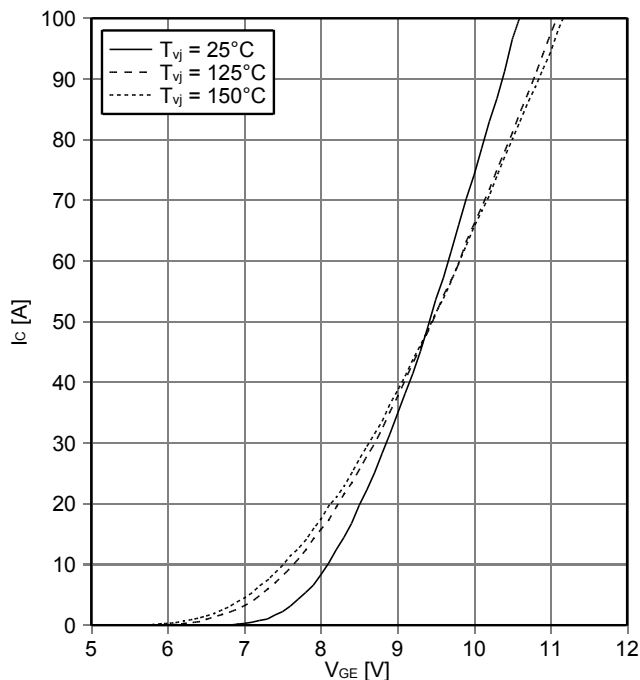
输出特性 IGBT, 逆变器 (典型)  
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$   
 $T_{vj} = 150^\circ\text{C}$



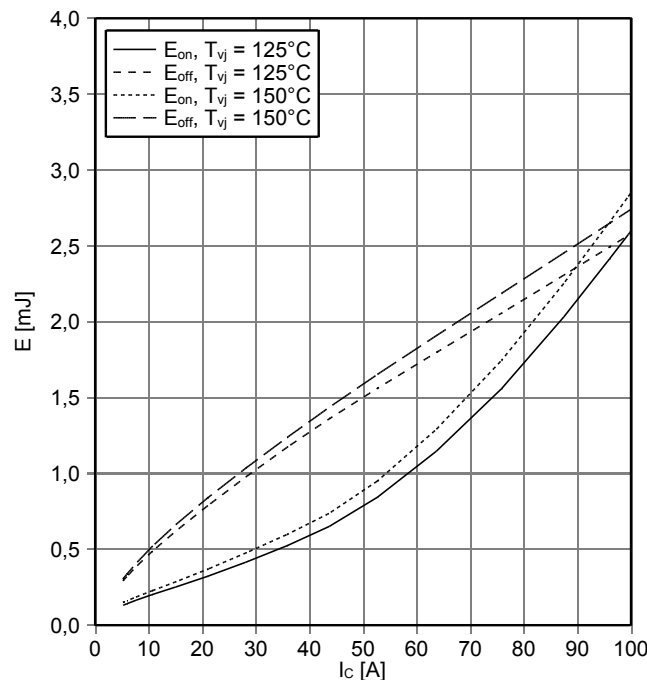
传输特性 IGBT, 逆变器 (典型)  
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)  
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$   
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 8.2\ \Omega, R_{Goff} = 8.2\ \Omega, V_{CE} = 300\text{ V}$



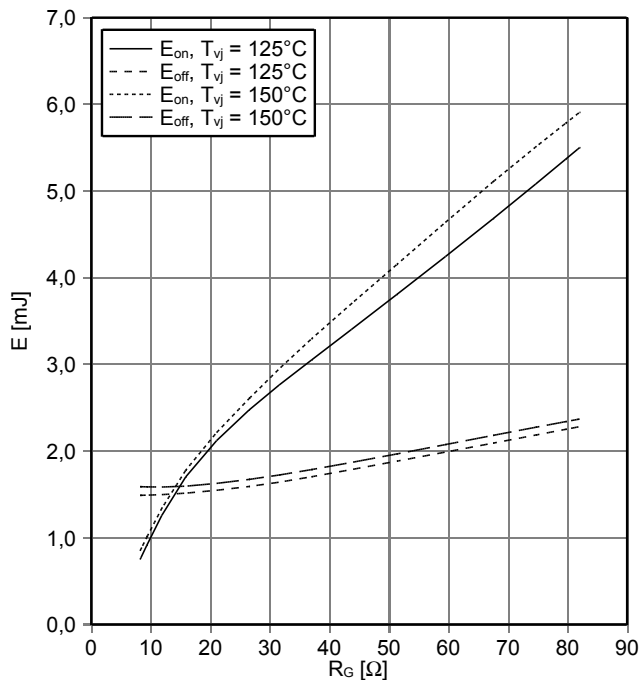
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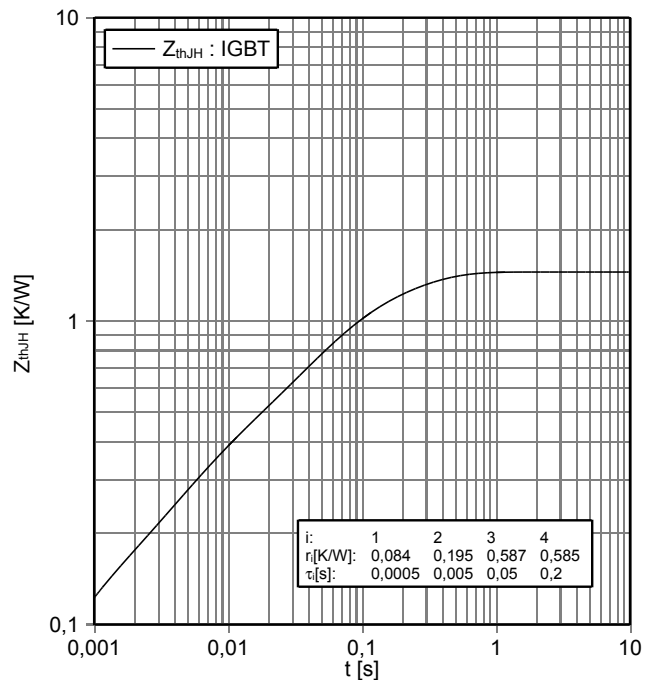
开关损耗 IGBT, 逆变器 (典型)  
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$   
 $V_{GE} = \pm 15 V, I_C = 50 A, V_{CE} = 300 V$



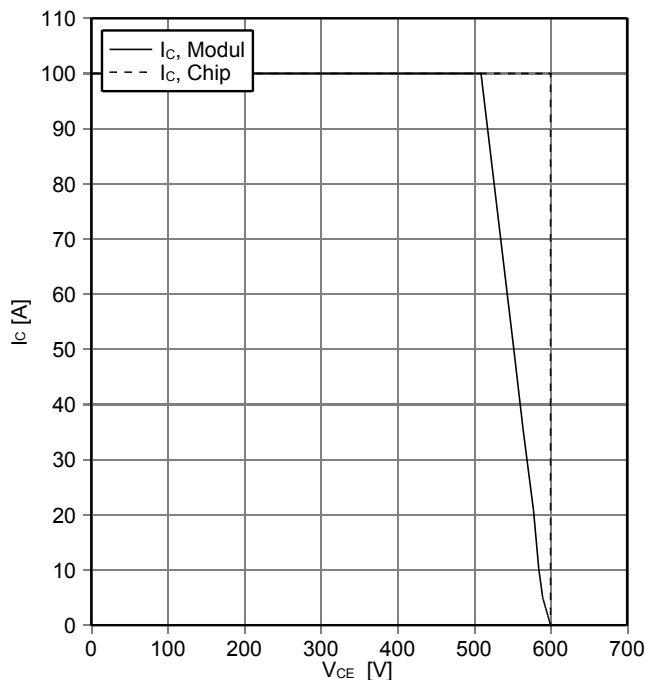
瞬态热阻抗 IGBT, 逆变器  
transient thermal impedance IGBT, Inverter

$Z_{thJH} = f(t)$



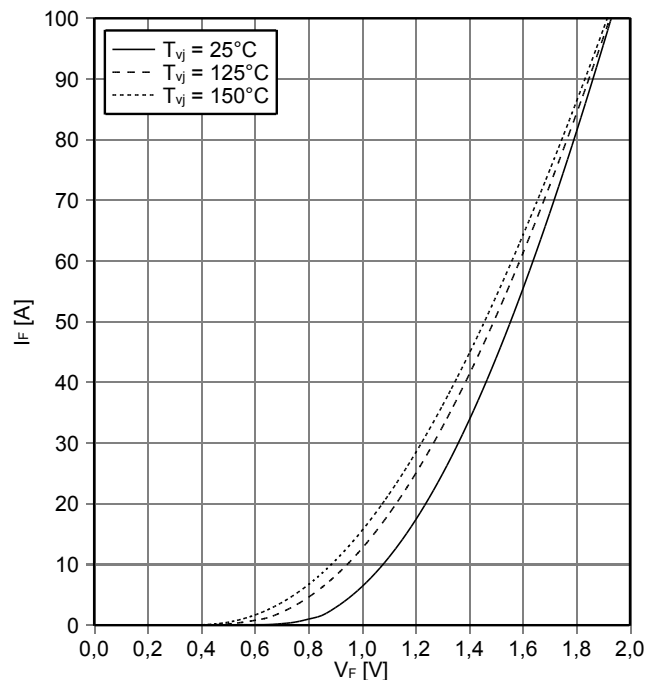
反偏安全工作区 IGBT, 逆变器 (RBSOA)  
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$   
 $V_{GE} = \pm 15 V, R_{Goff} = 8.2 \Omega, T_{vj} = 150^\circ C$



正向偏压特性 二极管, 逆变器 (典型)  
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



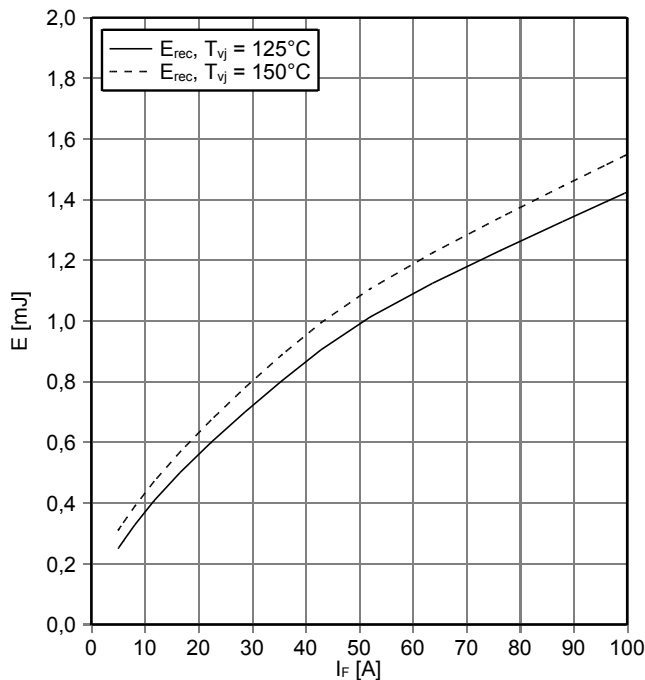
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初步数据  
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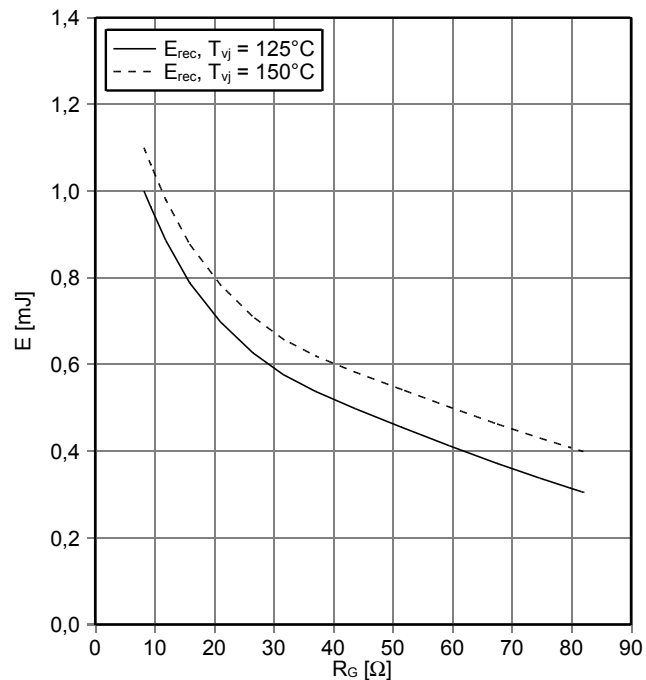
开关损耗 二极管, 逆变器 (典型)  
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$   
 $R_{Gon} = 8.2 \Omega, V_{CE} = 300 V$



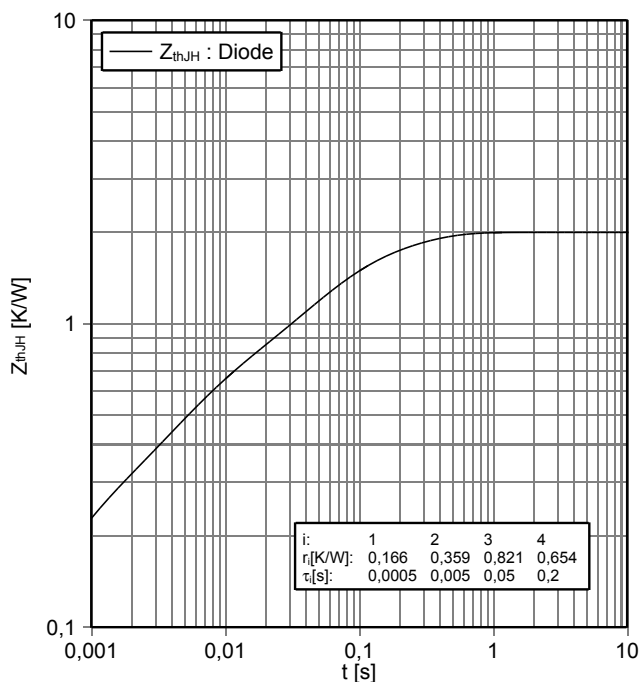
开关损耗 二极管, 逆变器 (典型)  
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$   
 $I_F = 50 A, V_{CE} = 300 V$



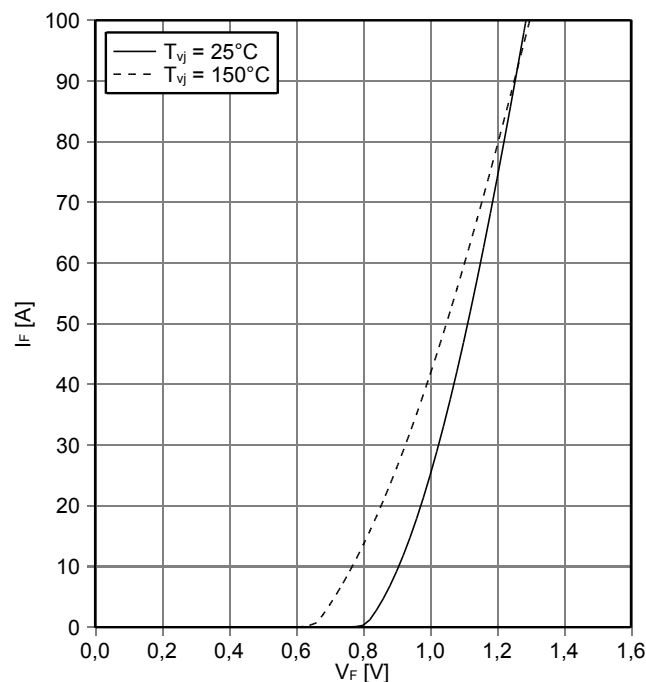
瞬态热阻抗 二极管, 逆变器  
transient thermal impedance Diode, Inverter

$Z_{thJH} = f(t)$



正向偏压特性 二极管, 整流器 (典型)  
forward characteristic of Diode, Rectifier (typical)

$I_F = f(V_F)$



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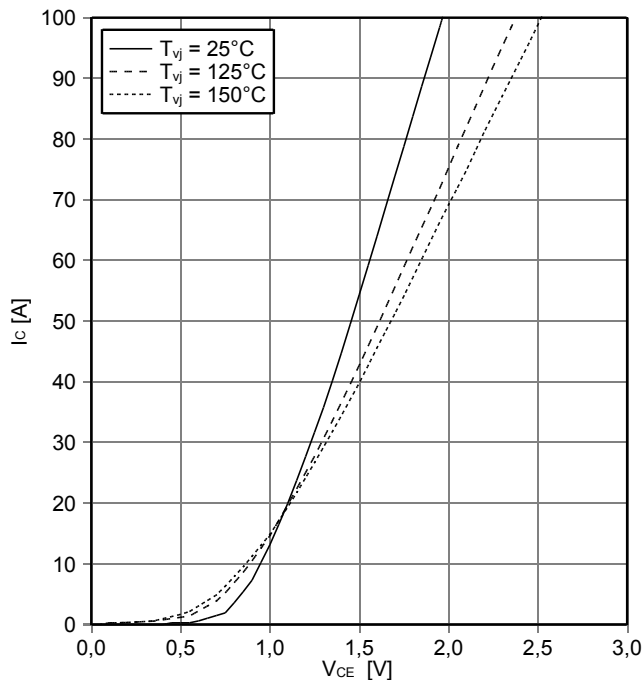




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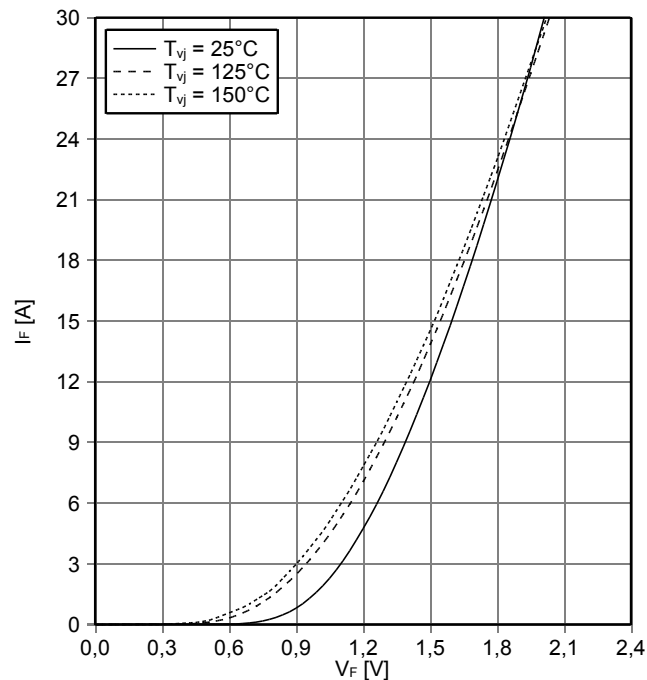
输出特性 IGBT, 制动-斩波器 (典型)  
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



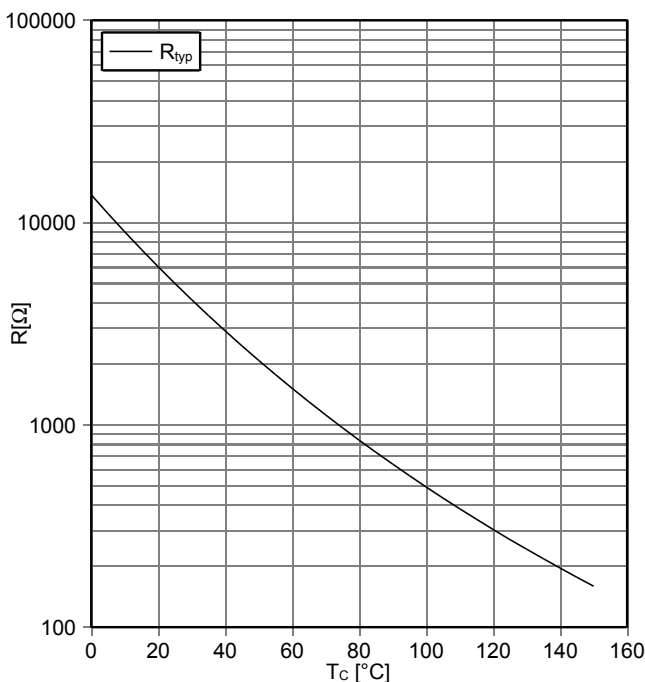
正向偏压特性 二极管, 制动-斩波器 (典型)  
forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$



负温度系数热敏电阻 温度特性  
NTC-Thermistor-temperature characteristic (typical)

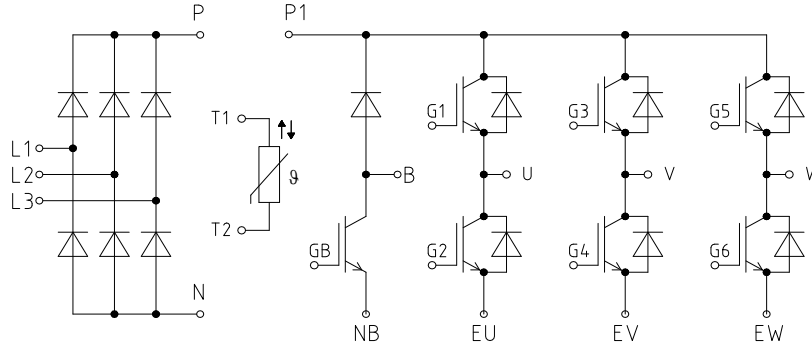
$R = f(T)$



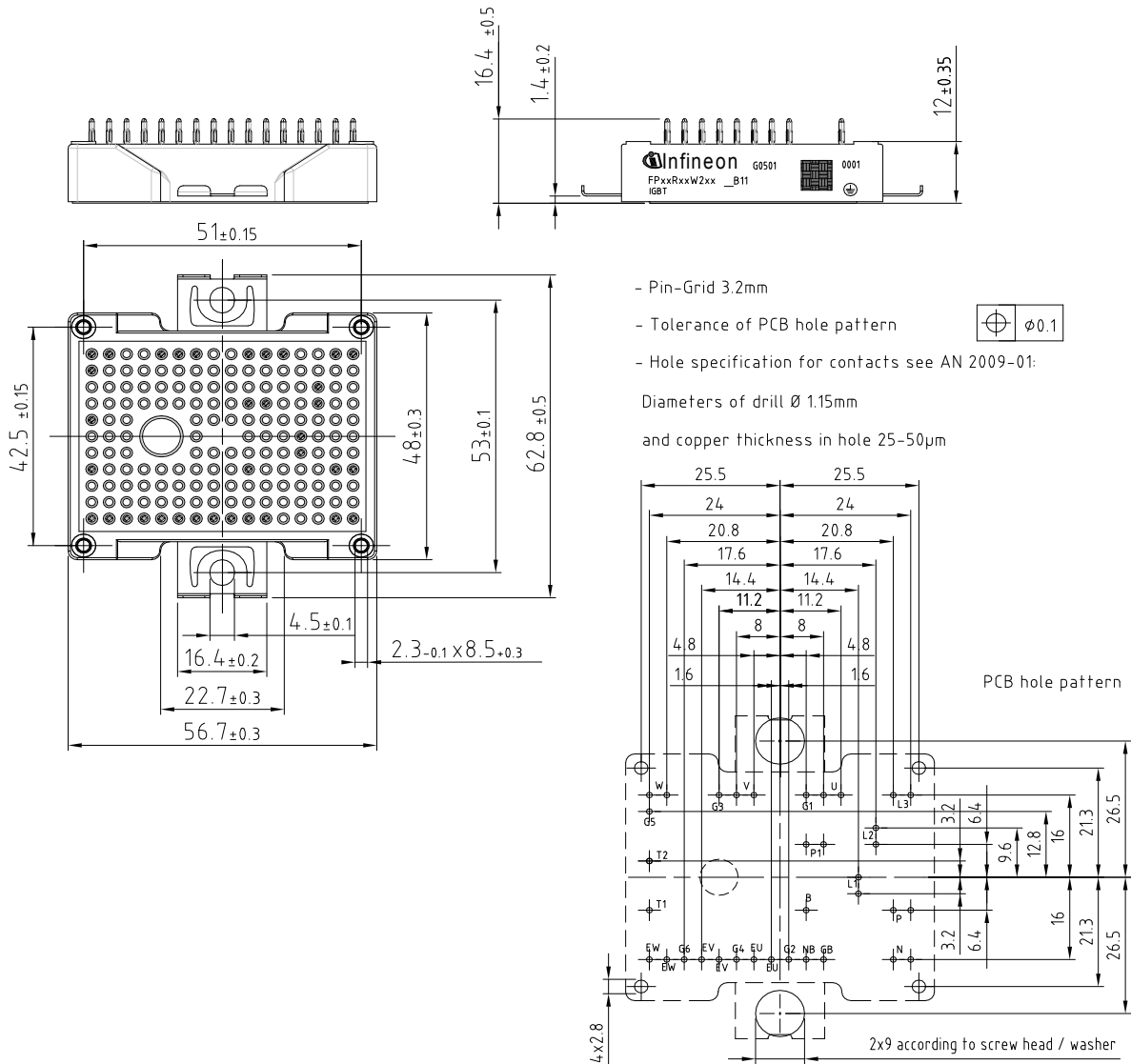
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初步数据  
Preliminary Data

接线图 / circuit\_diagram\_headline



封装尺寸 / package outlines



- Pin-Grid 3.2mm
- Tolerance of PCB hole pattern  $\begin{matrix} \oplus \\ \ominus \end{matrix} \phi 0.1$
- Hole specification for contacts see AN 2009-01:  
Diameters of drill  $\phi$  1.15mm  
and copper thickness in hole 25-50 $\mu$ m

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**初步数据  
Preliminary Data**

**使用条件和条款**

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-得到质量协议的结论

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如果有必要，请根据实际需要将类似的说明给你的客户

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- the conclusion of Quality Agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery depended on the realization of any such measures.

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